



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

DY227

TECHNICAL SPECIFICATIONS OF NPN EPITAXIAL PLANAR TRANSISTOR

Description

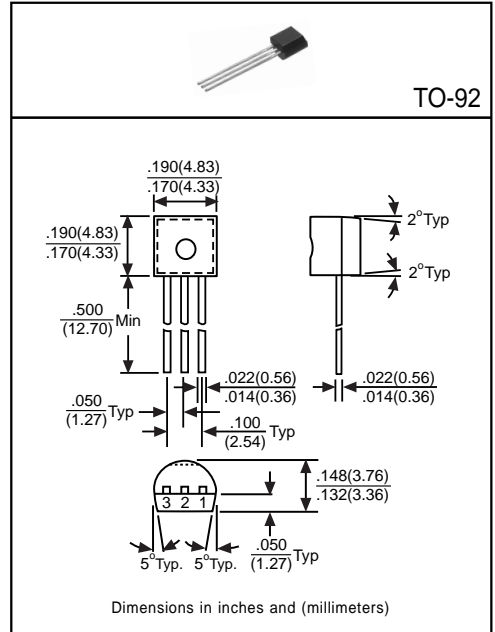
Designed for low frequency power amplifier applications.

Pinning

- 1 = Emitter
- 2 = Base
- 3 = Collector

Absolute Maximum Ratings (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	30	V
Collector-Emitter Voltage	V _{CE0}	25	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	300	mA
Total Power Dissipation	P _D	400	mW
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CB0}	30	-	-	V	I _C =100μA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CE0}	25	-	-	V	I _C =10mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EB0}	5	-	-	V	I _E =10μA, I _C =0
Collector Cutoff Current	I _{CBO}	-	-	100	nA	V _{CB} =25V, I _E =0
Emitter Cutoff Current	I _{EBO}	-	-	100	nA	V _{EB} =3V, I _C =0
Collector-Emitter Saturation Voltage ⁽¹⁾	V _{CE(sat)}	-	-	400	mV	I _C =300mA, I _B =30mA
DC Current Gain ⁽¹⁾	h _{FE}	70	-	400	-	I _C =50mA, V _{CE} =1V

(1) Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Classification of h_{FE}

Rank	O	Y	G
Range	70~140	120~240	200~400